

# MA2Z720

## Silicon epitaxial planar type

For high-frequency rectification

### ■ Features

- Sealed in S-mini type 2-pin package
- Allowing to rectify under ( $I_{F(AV)} = 500$  mA) condition
- Allowing high-density mounting

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	40	V
Peak reverse voltage	$V_{RM}$	40	V
Average forward current	$I_{F(AV)}$	500	mA
Non-repetitive peak forward surge current*	$I_{FSM}$	2	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

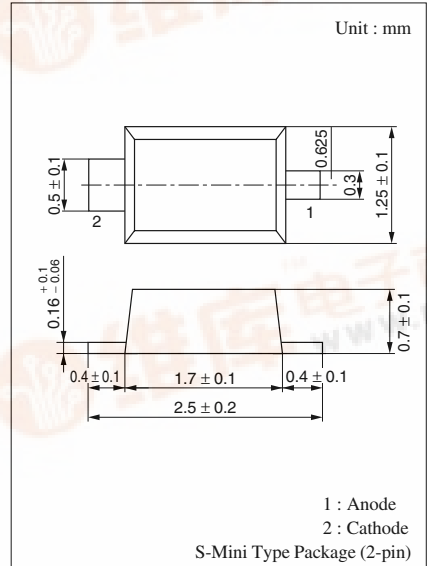
Note) \* : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 35$ V			100	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 500$ mA			0.55	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		60		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100$ mA, $I_{tr} = 0.1 I_R$ , $R_L = 100 \Omega$		5		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and leakage of current from the equipment used.

2. Rated input/output frequency: 400 MHz
3. \*:  $t_{rr}$  measuring instrument



Marking Symbol: 2L

